

# 74LVC1G80

Single D-type flip-flop; positive-edge trigger

Rev. 08 — 29 August 2007

Product data sheet

## 1. General description

The 74LVC1G80 provides a single positive-edge triggered D-type flip-flop.

Information on the data input is transferred to the  $\bar{Q}$  output on the LOW-to-HIGH transition of the clock pulse. The input pin D must be stable one set-up time prior to the LOW-to-HIGH clock transition for predictable operation.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

## 2. Features

- Wide supply voltage range from 1.65 V to 5.5 V
- High noise immunity
- Complies with JEDEC standard:
  - ◆ JESD8-7 (1.65 V to 1.95 V)
  - ◆ JESD8-5 (2.3 V to 2.7 V)
  - ◆ JESD8B/JESD36 (2.7 V to 3.6 V)
- $\pm 24$  mA output drive ( $V_{CC} = 3.0$  V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- ESD protection:
  - ◆ HBM JESD22-A114E exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V
- Specified from  $-40$  °C to  $+125$  °C

### 3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74LVC1G80GW	-40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74LVC1G80GV	-40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753
74LVC1G80GM	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886
74LVC1G80GF	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891

### 4. Marking

Table 2. Marking codes

Type number	Marking
74LVC1G80GW	VT
74LVC1G80GV	V80
74LVC1G80GM	VT
74LVC1G80GF	VT

### 5. Functional diagram

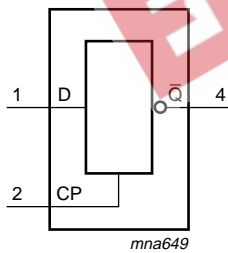


Fig 1. Logic symbol

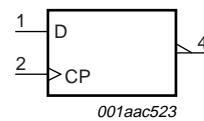
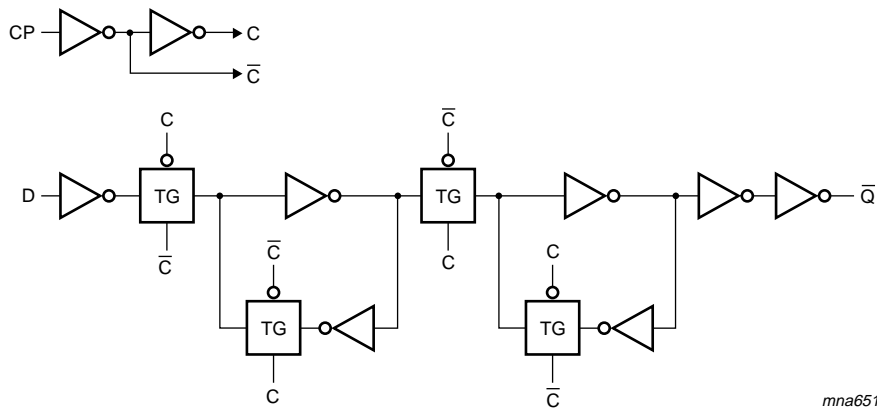


Fig 2. IEC logic symbol



mna651

Fig 3. Logic diagram

## 6. Pinning information

### 6.1 Pinning

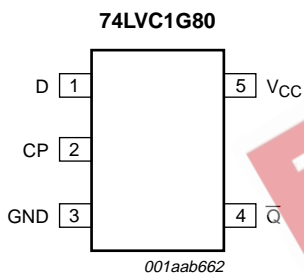


Fig 4. Pin configuration SOT353-1 and SOT753

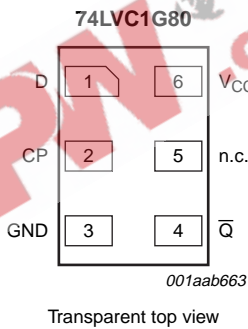


Fig 5. Pin configuration SOT886

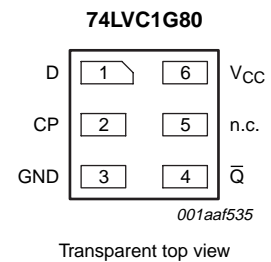


Fig 6. Pin configuration SOT891

### 6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT353-1/SOT753	SOT886/SOT891	
D	1	1	data input
CP	2	2	data pulse input
GND	3	3	ground (0 V)
Q̄	4	4	data output
n.c.	-	5	not connected
V <sub>CC</sub>	5	6	supply voltage

## 7. Functional description

Table 4. Function table<sup>[1]</sup>

Input		Output
CP	D	$\bar{Q}$
↑	L	H
↑	H	L
L	X	$\bar{q}$

- [1] H = HIGH voltage level;  
 L = LOW voltage level.  
 ↑ = LOW-to-HIGH CP transition;  
 X = don't care;  
 $\bar{q}$  = lower case letter indicates the state of referenced input, one set-up time prior to the LOW-to-HIGH CP transition.

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+6.5	V
$I_{IK}$	input clamping current	$V_I < 0$ V	-50	-	mA
$V_I$	input voltage		[1] -0.5	+6.5	V
$I_{OK}$	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V	-	±50	mA
$V_O$	output voltage	Active mode	[1][2] -0.5	$V_{CC} + 0.5$	V
		Power-down mode	[1][2] -0.5	+6.5	V
$I_O$	output current	$V_O = 0$ V to $V_{CC}$	-	±50	mA
$I_{CC}$	supply current		-	100	mA
$I_{GND}$	ground current		-100	-	mA
$P_{tot}$	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[3] -	250	mW
$T_{stg}$	storage temperature		-65	+150	°C

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.  
 [2] When  $V_{CC} = 0$  V (Power-down mode), the output voltage can be 5.5 V in normal operation.  
 [3] For TSSOP5 and SC-74A packages: above 87.5 °C the value of  $P_{tot}$  derates linearly with 4.0 mW/K.  
 For XSON6 packages: above 45 °C the value of  $P_{tot}$  derates linearly with 2.4 mW/K.

## 9. Recommended operating conditions

**Table 6. Recommended operating conditions**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>CC</sub>	supply voltage		1.65	-	5.5	V
V <sub>I</sub>	input voltage		0	-	5.5	V
V <sub>O</sub>	output voltage	Active mode	0	-	V <sub>CC</sub>	V
		V <sub>CC</sub> = 0 V; Power-down mode	0	-	5.5	V
T <sub>amb</sub>	ambient temperature		-40	-	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 1.65 V to 2.7 V	-	-	20	ns/V
		V <sub>CC</sub> = 2.7 V to 5.5 V	-	-	10	ns/V

## 10. Static characteristics

**Table 7. Static characteristics**

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ <sup>[1]</sup>	Max	Unit
<b>T<sub>amb</sub> = -40 °C to +85 °C</b>						
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7	-	-	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	2.0	-	-	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	0.7 × V <sub>CC</sub>	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	-	-	0.35 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	0.8	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	0.3 × V <sub>CC</sub>	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = -100 μA; V <sub>CC</sub> = 1.65 V to 5.5 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -4 mA; V <sub>CC</sub> = 1.65 V	1.2	-	-	V
		I <sub>O</sub> = -8 mA; V <sub>CC</sub> = 2.3 V	1.9	-	-	V
		I <sub>O</sub> = -12 mA; V <sub>CC</sub> = 2.7 V	2.2	-	-	V
		I <sub>O</sub> = -24 mA; V <sub>CC</sub> = 3.0 V	2.3	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = 100 μA; V <sub>CC</sub> = 1.65 V to 5.5 V	-	-	0.1	V
		I <sub>O</sub> = 4 mA; V <sub>CC</sub> = 1.65 V	-	-	0.45	V
		I <sub>O</sub> = 8 mA; V <sub>CC</sub> = 2.3 V	-	-	0.3	V
		I <sub>O</sub> = 12 mA; V <sub>CC</sub> = 2.7 V	-	-	0.4	V
		I <sub>O</sub> = 24 mA; V <sub>CC</sub> = 3.0 V	-	-	0.55	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 0 V to 5.5 V	-	±0.1	±5	μA
		V <sub>CC</sub> = 0 V; V <sub>I</sub> or V <sub>O</sub> = 5.5 V	-	±0.1	±10	μA

**Table 7. Static characteristics ...continued**

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ <sup>[1]</sup>	Max	Unit
I <sub>CC</sub>	supply current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 1.65 V to 5.5 V; I <sub>O</sub> = 0 A	-	0.1	10	μA
ΔI <sub>CC</sub>	additional supply current	per pin; V <sub>CC</sub> = 2.3 V to 5.5 V; V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A	-	5	500	μA
C <sub>I</sub>	input capacitance	V <sub>CC</sub> = 3.3 V; V <sub>I</sub> = GND to V <sub>CC</sub>	-	5	-	pF
<b>T<sub>amb</sub> = -40 °C to +125 °C</b>						
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7	-	-	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	2.0	-	-	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	0.7 × V <sub>CC</sub>	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	-	-	0.35 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	0.8	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	0.3 × V <sub>CC</sub>	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = -100 μA; V <sub>CC</sub> = 1.65 V to 5.5 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -4 mA; V <sub>CC</sub> = 1.65 V	0.95	-	-	V
		I <sub>O</sub> = -8 mA; V <sub>CC</sub> = 2.3 V	1.7	-	-	V
		I <sub>O</sub> = -12 mA; V <sub>CC</sub> = 2.7 V	1.9	-	-	V
		I <sub>O</sub> = -24 mA; V <sub>CC</sub> = 3.0 V	2.0	-	-	V
		I <sub>O</sub> = -32 mA; V <sub>CC</sub> = 4.5 V	3.4	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = 100 μA; V <sub>CC</sub> = 1.65 V to 5.5 V	-	-	0.1	V
		I <sub>O</sub> = 4 mA; V <sub>CC</sub> = 1.65 V	-	-	0.70	V
		I <sub>O</sub> = 8 mA; V <sub>CC</sub> = 2.3 V	-	-	0.45	V
		I <sub>O</sub> = 12 mA; V <sub>CC</sub> = 2.7 V	-	-	0.60	V
		I <sub>O</sub> = 24 mA; V <sub>CC</sub> = 3.0 V	-	-	0.80	V
		I <sub>O</sub> = 32 mA; V <sub>CC</sub> = 4.5 V	-	-	0.80	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 0 V to 5.5 V	-	-	±100	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>CC</sub> = 0 V; V <sub>I</sub> or V <sub>O</sub> = 5.5 V	-	-	±200	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 1.65 V to 5.5 V; I <sub>O</sub> = 0 A	-	-	200	μA
ΔI <sub>CC</sub>	additional supply current	per pin; V <sub>CC</sub> = 2.3 V to 5.5 V; V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A	-	-	5000	μA

[1] All typical values are measured at V<sub>CC</sub> = 3.3 V and T<sub>amb</sub> = 25 °C.

## 11. Dynamic characteristics

**Table 8. Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V). For test circuit see [Figure 9](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	
t <sub>pd</sub>	propagation delay	CP to $\bar{Q}$ ; see <a href="#">Figure 7</a> <sup>[2]</sup>						
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.0	3.4	9.9	1.0	13.0	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	0.5	2.3	7.0	0.5	9.0	ns
		V <sub>CC</sub> = 2.7 V	0.5	2.5	6.0	0.5	8.0	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	0.9	2.4	5.0	0.9	6.5	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	0.5	1.8	4.5	0.5	6.0	ns
t <sub>su</sub>	set-up time	HIGH or LOW; D to CP; see <a href="#">Figure 8</a> <sup>[3]</sup>						
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.3	0.8	-	2.3	-	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.5	0.6	-	1.5	-	ns
		V <sub>CC</sub> = 2.7 V	1.5	0.5	-	1.5	-	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.3	0.4	-	1.3	-	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	1.1	0.5	-	1.1	-	ns
t <sub>h</sub>	hold time	D to CP; see <a href="#">Figure 8</a>						
		V <sub>CC</sub> = 1.65 V to 1.95 V	0	-0.6	-	0	-	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	0	-0.4	-	0	-	ns
		V <sub>CC</sub> = 2.7 V	+0.5	-0.2	-	0.5	-	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	0.9	0.2	-	0.9	-	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	+0.5	-0.1	-	0.5	-	ns
t <sub>w</sub>	pulse width	CP HIGH or LOW; see <a href="#">Figure 8</a>						
		V <sub>CC</sub> = 1.65 V to 1.95 V	3.0	1.1	-	3.0	-	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	2.5	0.7	-	2.5	-	ns
		V <sub>CC</sub> = 2.7 V	2.5	0.6	-	2.5	-	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.5	0.6	-	2.5	-	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	2.0	0.5	-	2.0	-	ns
f <sub>max</sub>	maximum frequency	CP; see <a href="#">Figure 8</a>						
		V <sub>CC</sub> = 1.65 V to 1.95 V	160	300	-	160	-	MHz
		V <sub>CC</sub> = 2.3 V to 2.7 V	160	350	-	160	-	MHz
		V <sub>CC</sub> = 2.7 V	160	350	-	160	-	MHz
		V <sub>CC</sub> = 3.0 V to 3.6 V	160	350	-	160	-	MHz
		V <sub>CC</sub> = 4.5 V to 5.5 V	200	400	-	200	-	MHz
C <sub>PD</sub>	power dissipation capacitance	V <sub>I</sub> = GND to V <sub>CC</sub> ; V <sub>CC</sub> = 3.3 V <sup>[4]</sup>	-	17	-	-	-	pF

[1] Typical values are measured at T<sub>amb</sub> = 25 °C and V<sub>CC</sub> = 1.8 V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.

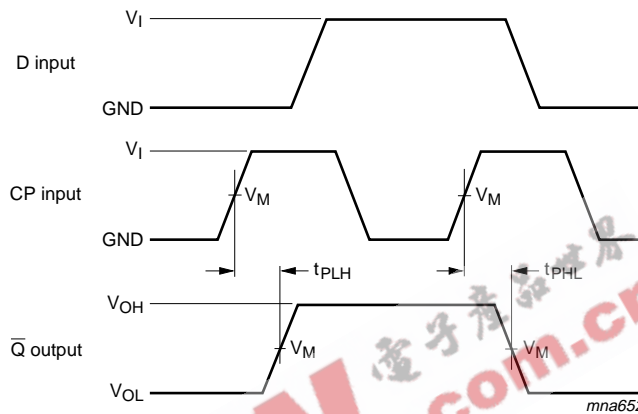
[2] t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>.

[3] t<sub>su</sub> is the same as t<sub>su(H)</sub> and t<sub>su(L)</sub>.

[4] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW).

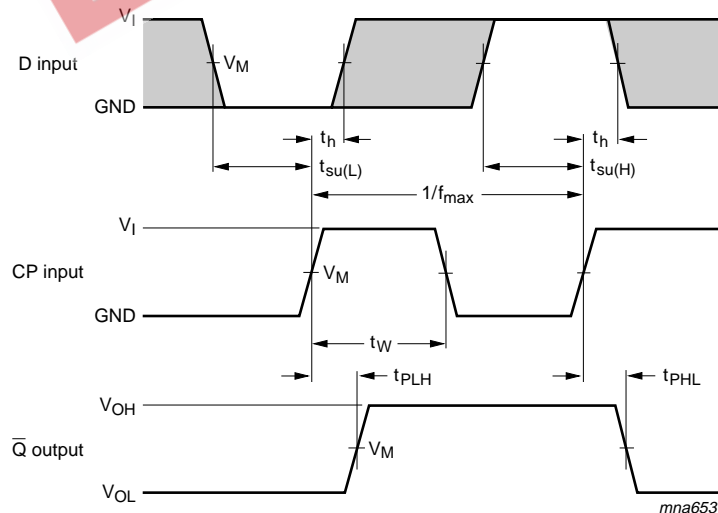
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o)$  where:  
 $f_i$  = input frequency in MHz;  
 $f_o$  = output frequency in MHz;  
 $C_L$  = output load capacitance in pF;  
 $V_{CC}$  = supply voltage in V;  
 $N$  = number of inputs switching;  
 $\sum(C_L \times V_{CC}^2 \times f_o)$  = sum of outputs.

## 12. Waveforms



Measurement points are given in [Table 9](#).  
 $V_{OL}$  and  $V_{OH}$  are typical output voltage levels that occur with the output.

**Fig 7. Clock (CP) to output ( $\bar{Q}$ ) propagation delay times**



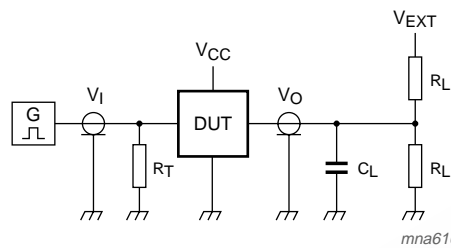
Measurement points are given in [Table 9](#).  
 $V_{OL}$  and  $V_{OH}$  are typical output voltage levels that occur with the output.  
 The shaded areas indicate when the input is permitted to change for predictable output performance.

**Fig 8. Clock (CP) to output ( $\bar{Q}$ ) propagation delay times, clock pulse width, D to set-up times, the CP to D hold times and maximum clock pulse frequency**



Table 9. Measurement points

Supply voltage	Input	Output
$V_{CC}$	$V_M$	$V_M$
1.65 V to 1.95 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.3 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$



Test data is given in [Table 10](#).

Definitions for test circuit:

$R_L$  = Load resistance.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_T$  = Termination resistance should be equal to the output impedance  $Z_o$  of the pulse generator.

$V_{EXT}$  = External voltage for measuring switching times.

Fig 9. Load circuitry for switching times

Table 10. Test data

Supply voltage	Input		Load		$V_{EXT}$
$V_{CC}$	$V_I$	$t_r = t_f$	$C_L$	$R_L$	$t_{PLH}, t_{PHL}$
1.65 V to 1.95 V	$V_{CC}$	$\leq 2.0$ ns	30 pF	1 k $\Omega$	open
2.3 V to 2.7 V	$V_{CC}$	$\leq 2.0$ ns	30 pF	500 $\Omega$	open
2.7 V	2.7 V	$\leq 2.5$ ns	50 pF	500 $\Omega$	open
3.0 V to 3.6 V	2.7 V	$\leq 2.5$ ns	50 pF	500 $\Omega$	open
4.5 V to 5.5 V	$V_{CC}$	$\leq 2.5$ ns	50 pF	500 $\Omega$	open

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1

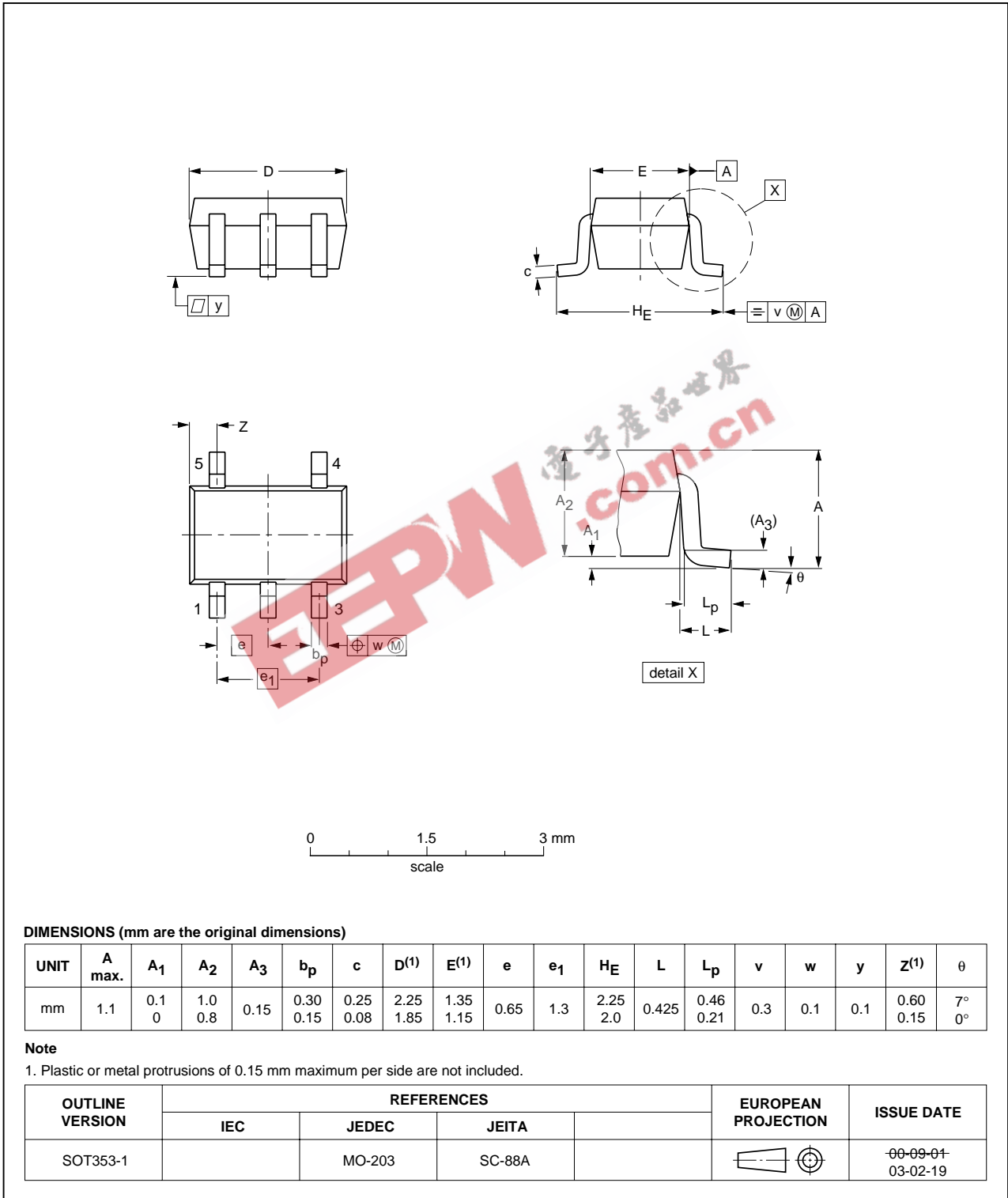


Fig 10. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

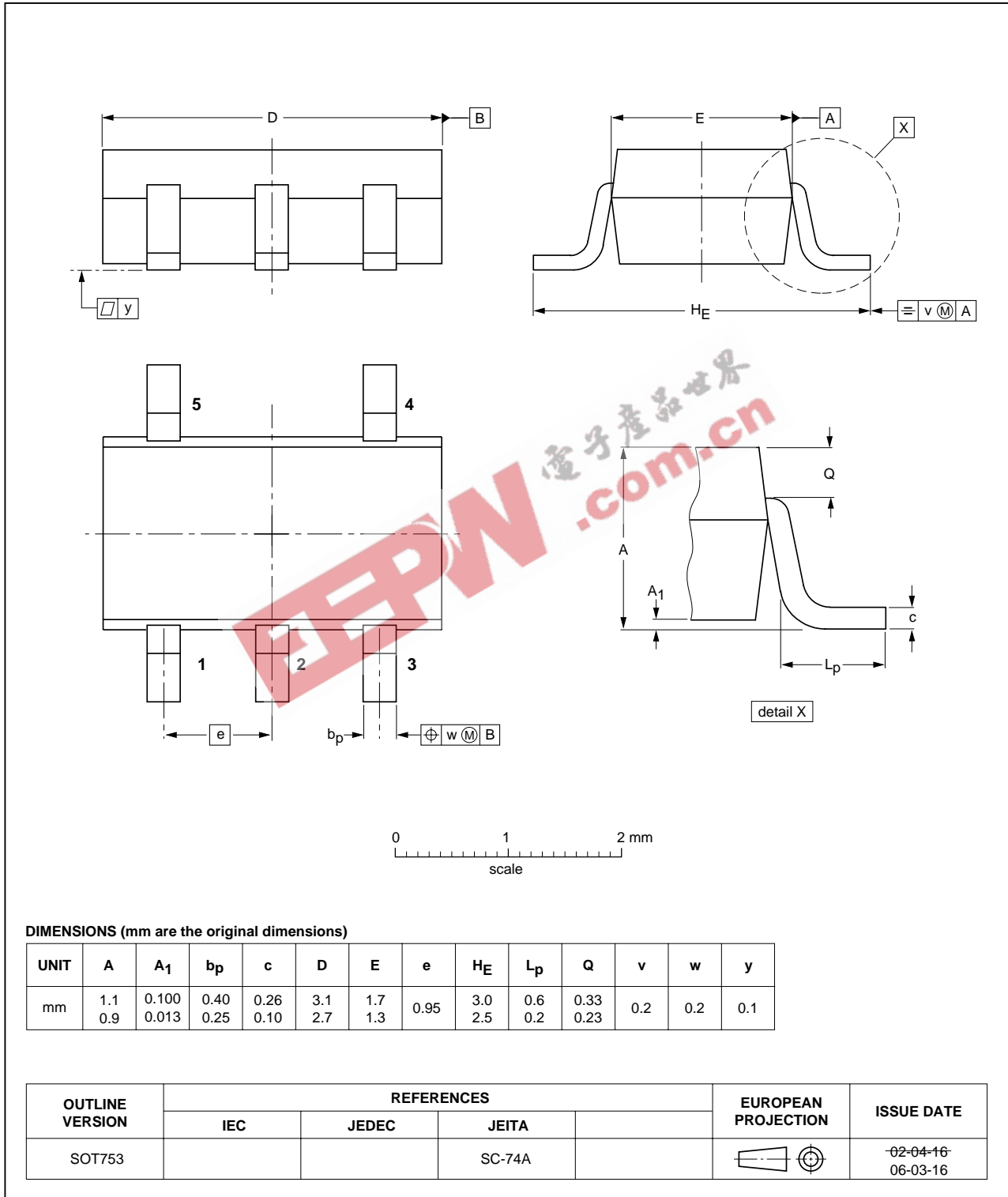


Fig 11. Package outline SOT753 (SC-74A)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886

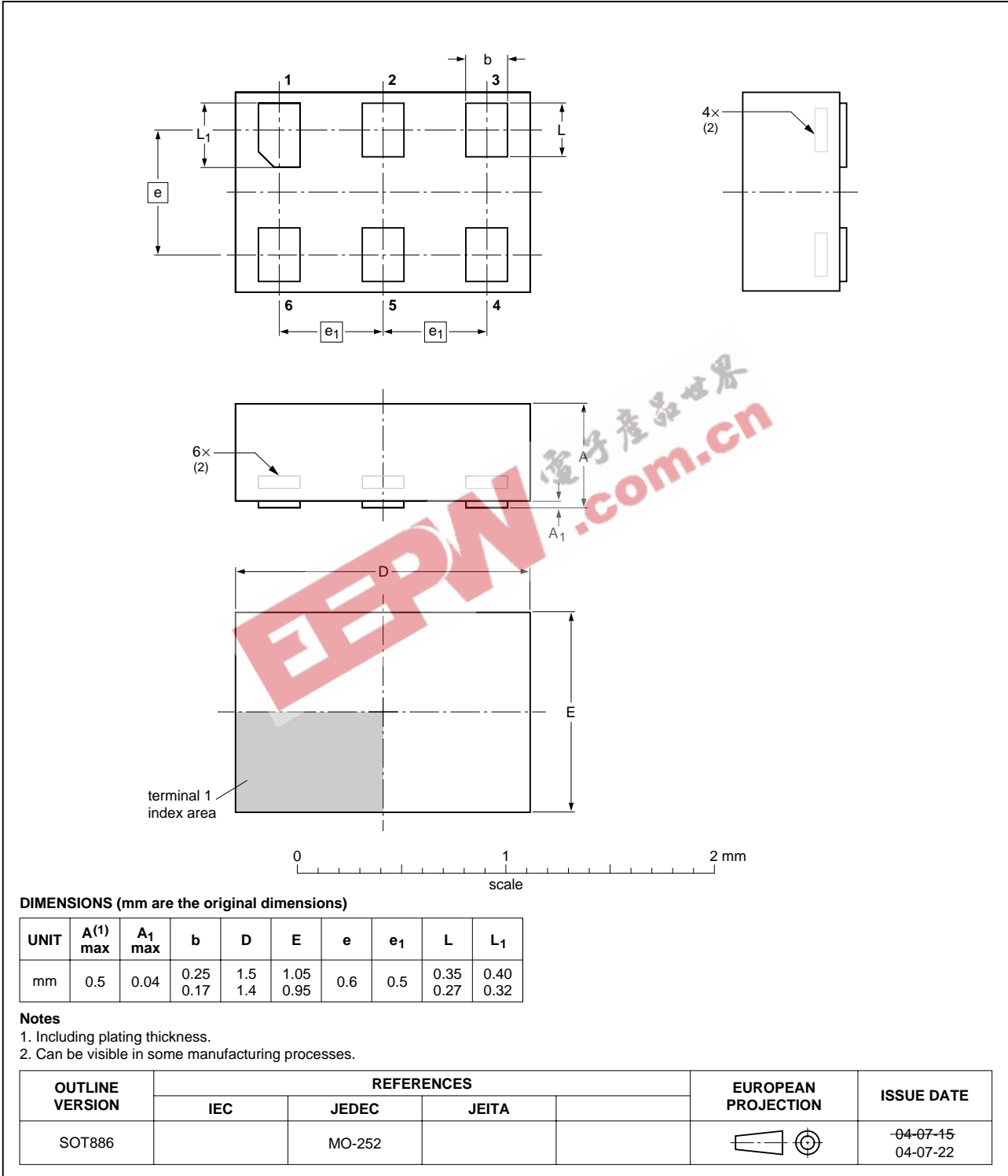


Fig 12. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

SOT891

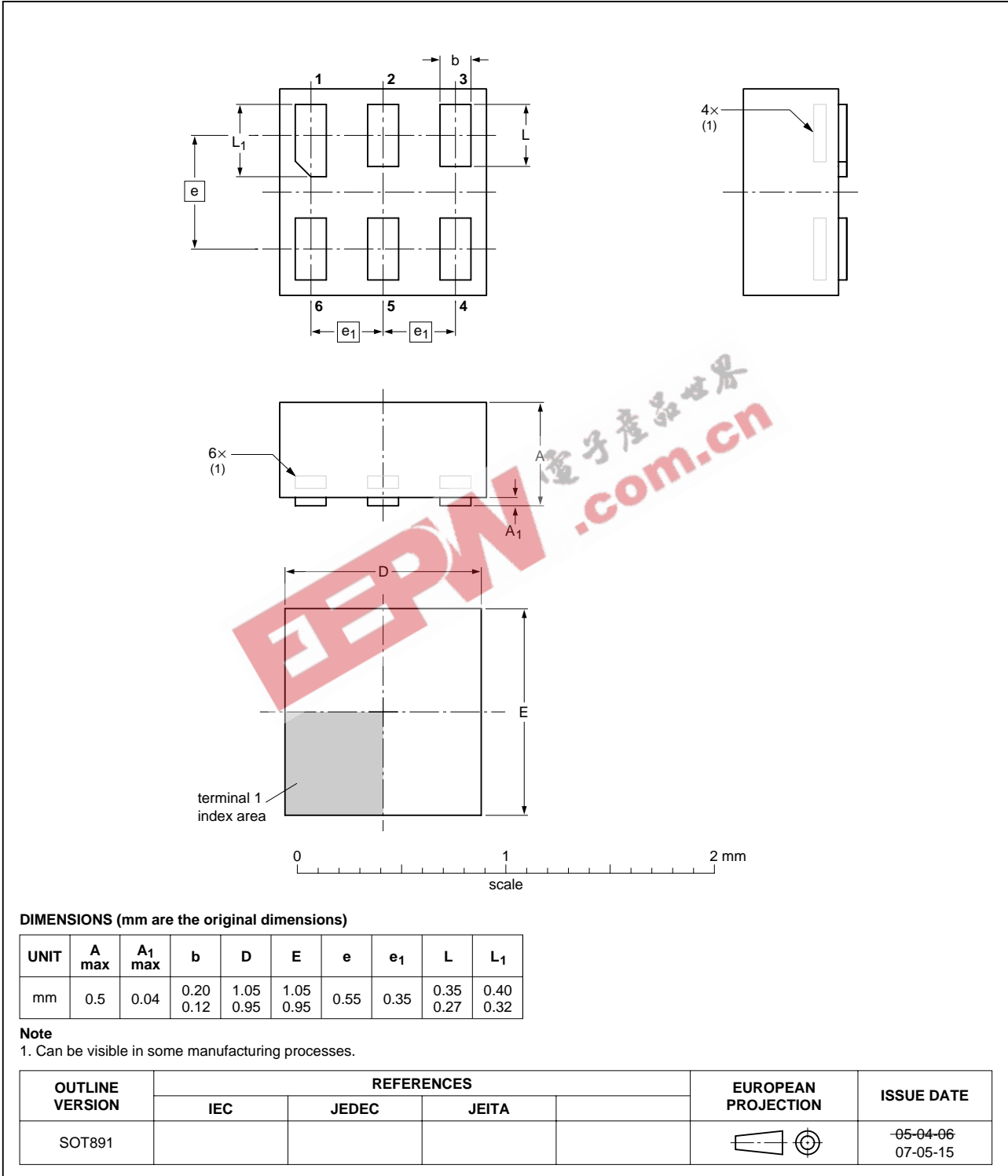


Fig 13. Package outline SOT891 (XSON6)

## 14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

## 15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1G80_8	20070829	Product data sheet	-	74LVC1G80_7
Modifications:	<ul style="list-style-type: none"> <li>In <a href="#">Section 10 "Static characteristics"</a>, changed conditions for input leakage and supply current.</li> <li><a href="#">Figure 13 "Package outline SOT891 (XSON6)"</a> updated.</li> </ul>			
74LVC1G80_7	20061012	Product data sheet	-	74LVC1G80_6
74LVC1G80_6	20040910	Product specification	-	74LVC1G80_5
74LVC1G80_5	20040629	Product specification	-	74LVC1G80_4
74LVC1G80_4	20040429	Product specification	-	74LVC1G80_3
74LVC1G80_3	20030526	Product specification	-	74LVC1G80_2
74LVC1G80_2	20030130	Product specification	-	74LVC1G80_1
74LVC1G80_1	20010404	Product specification	-	-

## 16. Legal information

### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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